



8. An semiconductor device as set forth in Claim

1, further comprising:

a barrier metal layer made of Ni or a metal having Ni as its main component, on an entire top surface of said main conductor layer.

9. The semiconductor device as set forth in Claim 8, wherein said barrier metal layer covers side surfaces of said main conductor layer.

10. An semiconductor device as set forth in Claim 1, further comprising:

a foundation metal layer made of Ti, Ti-W, Cr, or a metal having any of those elements as its main component, under said main conductor layer.

11. A manufacturing method of a semiconductor device, comprising the steps of:

forming a foundation metal layer on a semiconductor substrate on which formed are a plurality of electrode pads and a first insulating layer having first opening sections on said electrode pads;

forming a photosensitive first resist on said foundation metal layer;

forming, in said first resist, a plurality of first resist opening sections for exposing said

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forming protrudent electrodes on said metal layer.

forming a barrier metal layer in said enlarged first resist opening sections.

13. A manufacturing method of a semiconductor device as set forth in Claim 11, further comprising the step of:

forming a metal layer on said main conductor layer by electroless plating of a raw material different from said main conductor layer, after the step of removing said foundation metal layer.

14. A manufacturing method of a semiconductor device, comprising the steps of:

forming a foundation metal layer on a semiconductor substrate on which formed are a plurality of electrode pads and a first insulating layer having first opening sections on said electrode pads;

forming a photosensitive first resist on said foundation metal layer;

forming, in said first resist, a plurality of first resist opening sections for exposing said electrode pads;

forming a main conductor layer in said first resist opening sections;

removing said first resist;

removing said foundation metal layer by use of said main conductor layer as a photo mask;

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first resist opening section.

16. A manufacturing method of a semiconductor device as set forth in Claim 14, further comprising the step of:

forming a metal layer on said main conductor layer by electroless plating of a raw material different from said main conductor layer, after the step of removing said foundation metal layer.

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